

Silicon NPN Power Transistors

2SC4303

DESCRIPTION

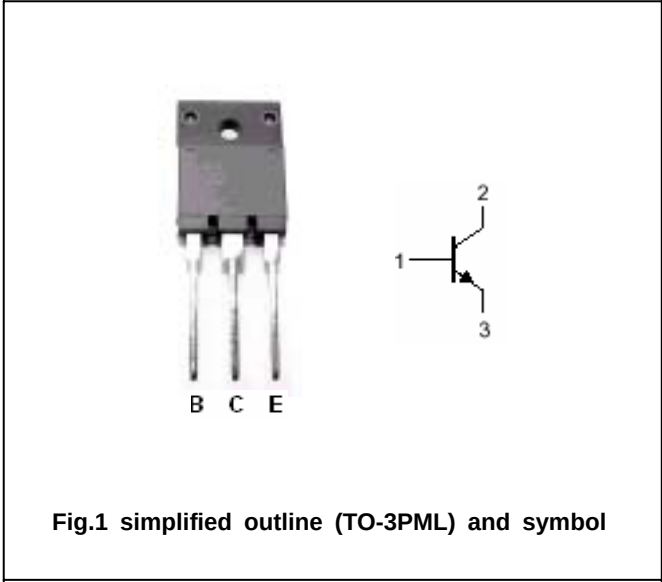
- With TO-3PML package
- High voltage switchihg transistor

APPLICATIONS

- Switching Regulator,
- Lighting Inverter and general purpose

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1400	V
V_{CEO}	Collector-emitter voltage	Open base	800	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		6	A
P_C	Collector power dissipation	$T_C=25^{\circ}C$	80	W
T_j	Junction temperature		150	$^{\circ}C$
T_{stg}	Storage temperature		-55~150	$^{\circ}C$

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CHARACTERISTICST_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA; I _B =0	800			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA; I _C =0	7			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =2.5A; I _B =0.5A			1.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =2.5A; I _B =0.5A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =1200V; I _E =0			100	μA
I _{EBO}	Emitter cut-off current	V _{EB} =7V; I _C =0			100	μA
h _{FE}	DC current gain	I _C =2.5A ; V _{CE} =4V	6			
f _T	Transition frequency	I _E =0.5A ; V _{CE} =12V		4		MHz

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PACKAGE OUTLINE

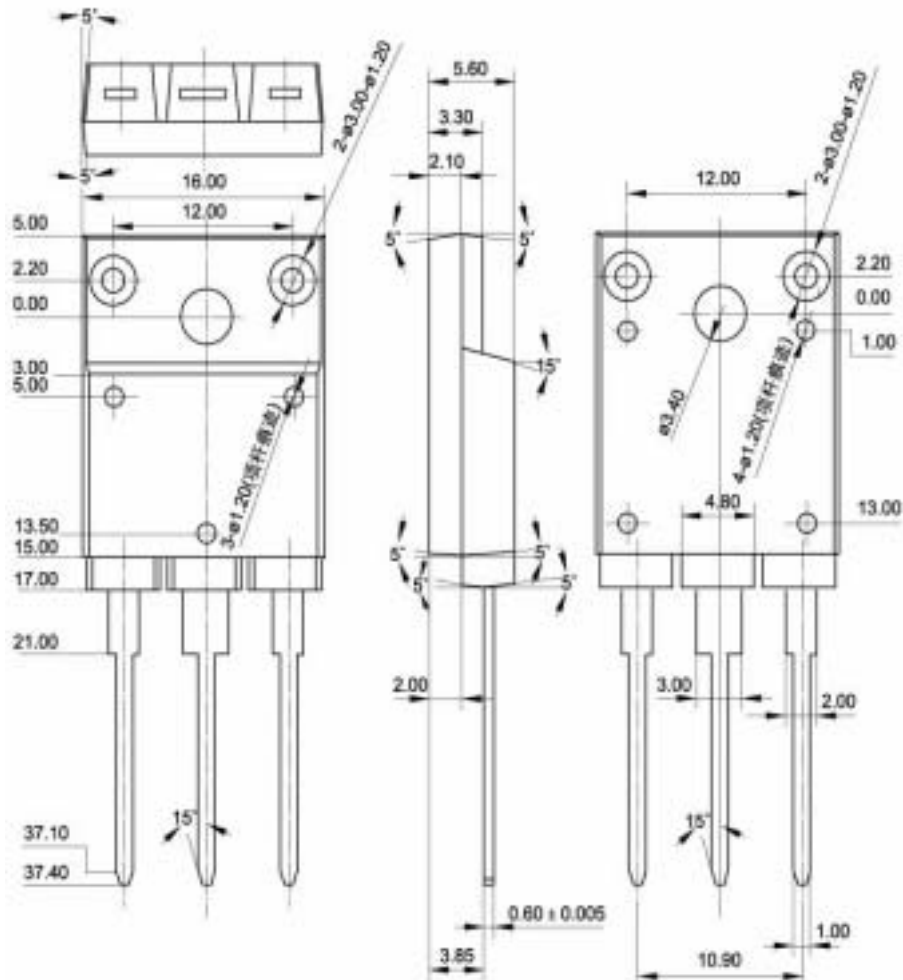


Fig.2 Outline dimensions